



20V Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

20 / -20V

Current

1/-0.7A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

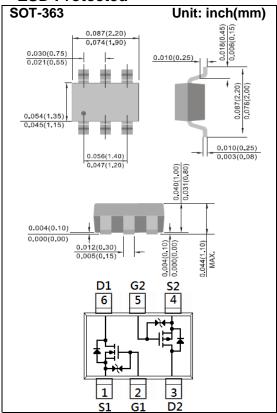
Mechanical Data

• Case: SOT-363 Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0002 ounces, 0.006 grams

Marking: T60



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	20 -20		V
Gate-Source Voltage		V_{GS}	<u>+</u> 8 <u>+</u> 8		V
Continuous Drain Current		I _D	1	-0.7	Α
Pulsed Drain Current (Note 4)		I _{DM}	4	-2.8	Α
Barres Biratinatian	T _a =25°C	Б	35	mW	
Power Dissipation	Derate above 25°C	P _D	2	mW/°C	
Operating Junction and Storage Tem	T_J, T_{STG}	-55~	°C		
Typical Thermal resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	357		°C/W





N-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_{D} = 250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.8	1.0	V
Drain-Source On-State Resistance		V_{GS} = 4.5V, I_{D} = 1A	-	114	150	mΩ
	R _{DS(on)}	V_{GS} = 2.5V, I_{D} = 0.7A	-	160	215	
		V_{GS} = 1.8V, I_{D} = 0.3A	-	280	400	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 8V, V _{DS} =0V	-	<u>+</u> 2	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	Q_{g}	\/ 40\/ L 4A	-	1.6	-	nC
Gate-Source Charge	Q_gs	V_{DS} =10V, I_{D} =1A, V_{GS} =4.5V (Note 1,2)	-	0.3	-	
Gate-Drain Charge	Q_gd		-	0.41	-	
Input Capacitance	Ciss	\/ 40\/ \/ 0\/	-	92	-	pF
Output Capacitance	Coss	V _{DS} =10V, V _{GS} =0V, f=1.0MHZ	-	25	-	
Reverse Transfer Capacitance	Crss		-	9.1	-	
Switching						
Turn-On Delay Time	td _(on)	10111111	-	5.8	-	ns
Turn-On Rise Time	tr	V _{DD} =10V, I _D =1A,	-	25.7	-	
Turn-Off Delay Time	td _(off)	V_{GS} =4.5V, R_G =6 Ω (Note 1,2)	-	41	-	
Turn-Off Fall Time	tf		-	31	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			_	_	1	Α
Diode Forward Current	I _S		_	-	ı	A
Diode Forward Voltage	V_{SD}	I _S = 1A, V _{GS} =0V	-	0.85	1.2	V





P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D = -250uA	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.5	-0.64	-1	V
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} = -4.5V, I_{D} = -0.7A	-	260	325	mΩ
		V_{GS} = -2.5V, I_{D} = -0.6A	-	310	420	
		V_{GS} = -1.8V, I_{D} = -0.5A	-	400	600	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 8V, V _{DS} =0V	-	<u>+</u> 3.5	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	Q_g	V _{DS} =-10V, I _D =-0.7A, V _{GS} =-4.5V ^(Note 1,2)	-	2.2	-	nC
Gate-Source Charge	Q_gs		-	0.4	-	
Gate-Drain Charge	Q_gd		-	0.5	-	
Input Capacitance	Ciss	10\/ \/ 0\/	-	151	-	pF
Output Capacitance	Coss	V_{DS} =-10V, V_{GS} =0V, f=1.0MHZ	-	27	-	
Reverse Transfer Capacitance	Crss	I=1.UIVIDZ	-	8.8	-	
Switching						
Turn-On Delay Time	td _(on)	101/ 1 0 70	-	2.2	-	ns
Turn-On Rise Time	tr	V_{DD} =-10V, I_{D} =-0.7A, V_{GS} =-4.5V, R_{G} =6 Ω (Note 1,2)	-	19.2	-	
Turn-Off Delay Time	td _(off)		-	6.2	-	
Turn-Off Fall Time	tf		-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	-1	А
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.86	-1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.

4. The maximum current rating is package limited.





N-Channel TYPICAL CHARACTERISTIC CURVES

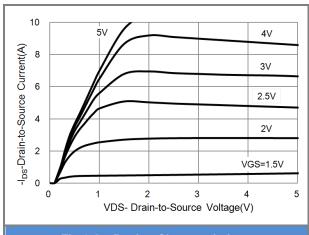


Fig.1 On-Region Characteristics

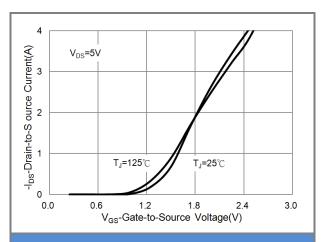


Fig.2 Transfer Characteristics

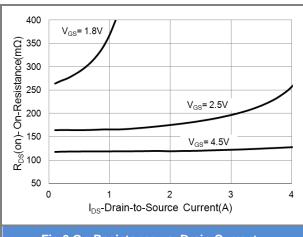


Fig.3 On-Resistance vs. Drain Current

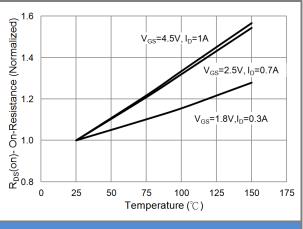
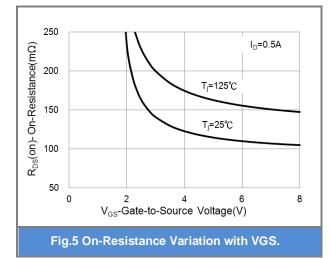


Fig.4 On-Resistance vs. Junction temperature



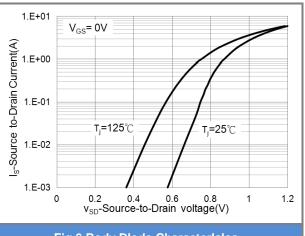


Fig.6 Body Dlode CharacterIslcs





N-Channel TYPICAL CHARACTERISTIC CURVES

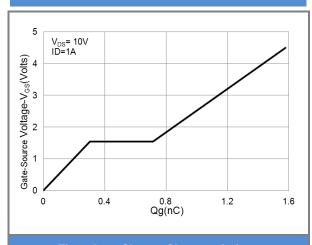


Fig.7 Gate-Charge Characteristics

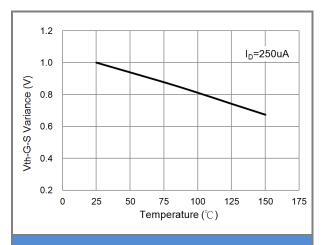


Fig.8 Threshold Voltage Variation with Temperature.

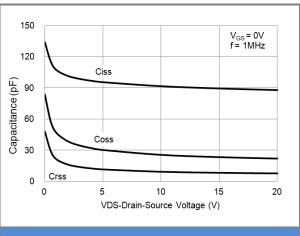


Fig.9 Capacitance vs. Drain-Source Voltage.





P-Channel TYPICAL CHARACTERISTIC CURVES

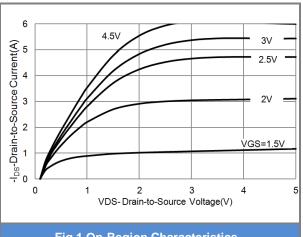


Fig.1 On-Region Characteristics

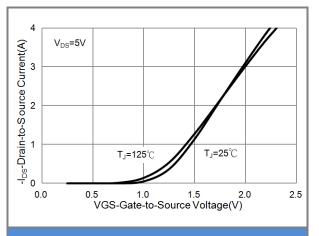


Fig.2 Transfer Characteristics

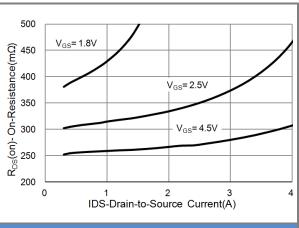


Fig.3 On-Resistance vs. Drain Current

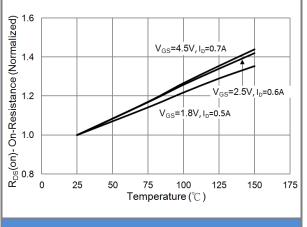
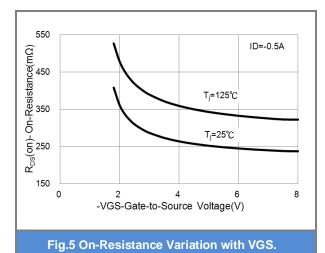
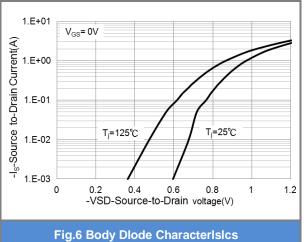


Fig.4 On-Resistance vs. Junction temperature









P-Channel TYPICAL CHARACTERISTIC CURVES

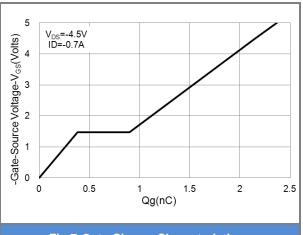


Fig.7 Gate-Charge Characteristics

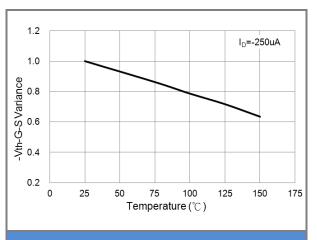


Fig.8 Threshold Voltage Variation with Temperature.

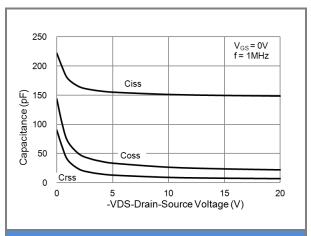


Fig.9 Threshold Voltage Variation with Temperature.

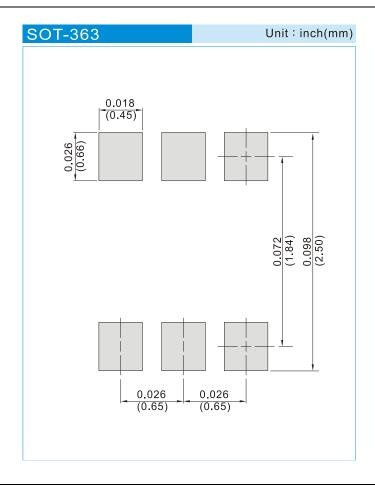




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJT7600_R1_00001	SOT-363	3K pcs / 7" reel	T60	Halogen free
PJT7600_R2_00001	SOT-363	10K pcs / 13" reel	T60	Halogen free

MOUNTING PAD LAYOUT







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